Fang Song

List of Publications by Year
in descending order

10	278	1040056 9	1372567 10
papers	citations	h-index	g-index

10	10	10	314
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A bio-inspired physically transient/biodegradable synapse for security neuromorphic computing based on memristors. Nanoscale, 2018, 10, 20089-20095.	5.6	82
2	Physically Transient Threshold Switching Device Based on Magnesium Oxide for Security Application. Small, 2018, 14, e1800945.	10.0	44
3	ZnO-Based Physically Transient and Bioresorbable Memory on Silk Protein. IEEE Electron Device Letters, 2018, 39, 31-34.	3.9	42
4	Solution-Processed Physically Transient Resistive Memory Based on Magnesium Oxide. IEEE Electron Device Letters, 2019, 40, 193-195.	3.9	23
5	Physically Transient Memristor Synapse Based on Embedding Magnesium Nanolayer in Oxide for Security Neuromorphic Electronics. IEEE Electron Device Letters, 2019, 40, 1265-1268.	3.9	22
6	Dissolvable and biodegradable resistive switching memory based on magnesium oxide. IEEE Electron Device Letters, 2016, , 1-1.	3.9	19
7	Polarization Engineering in PZT/AlGaN/GaN High-Electron-Mobility Transistors. IEEE Transactions on Electron Devices, 2018, 65, 3149-3155.	3.0	16
8	Physically Transient Memristive Synapse With Short-Term Plasticity Based on Magnesium Oxide. IEEE Electron Device Letters, 2019, 40, 706-709.	3.9	16
9	Physically Transient Resistive Switching Memory With Material Implication Operation. IEEE Electron Device Letters, 2019, 40, 1618-1621.	3.9	10
10	Physically Transient Resistive Memory With Programmable Switching Behaviors in MgO-Mo Based Devices. IEEE Electron Device Letters, 2020, 41, 553-556.	3.9	4